

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device has a semiconductor substrate 4; a first interlayer insulating film ~~2 formed~~ on the semiconductor substrate, and having first contact holes; first contact plugs ~~12 and 13 formed on the first interlayer insulating film 2 and~~ having portions buried in the first contact holes and portions protruded protruding from the surface of the first interlayer insulating film ~~2~~; sidewalls ~~15 formed~~ on the sides of the protruded protruding portions of the first contact plugs ~~12 and 13~~; a second interlayer insulating film ~~16 formed~~ on the first interlayer insulating film ~~2~~, the first contact plugs ~~12 and 13~~, and the sidewalls ~~15~~, and having second contact holes; and second contact plugs ~~19 and 20 formed on in~~ the second contact holes, and connected to the first contact plugs ~~12 and 13~~.